TOSHIBA Photocoupler GaAlAs IRED + Photo IC

TLP700

Industrial inverters
Inverter for air conditioners
IGBT/Power MOS FET gate drive

TLP700 consists of a GaAlAs light-emitting diode and an integrated photodetector.

This unit is 6-lead SDIP package. The TLP700 is 50% smaller than the 8-pin DIP and meets the reinforced insulation class requirements of international safety standards. Therefore the mounting area can be reduced in equipment requiring safety standard certification.

The TLP700 is suitable for gate driving circuits for IGBTs or power MOSFETs. In particular, the TLP700 is capable of "direct" gate driving of low-power IGBTs.

Peak output current : ±2.0 A (max)
 Guaranteed performance over temperature : -40~100°C
 Supply current : 2 mA (max)
 Power supply voltage : 15~30 V

Threshold input current : I_{FLH} = 5 mA (max)
 Switching time (t_{pLH} / t_{pHL}) : 500 ns (max)
 Common mode transient immunity : ±10 kV/µs (min)
 Isolation voltage : 5000 Vrms (min)

Construction mechanical rating

	7.62-mm pitch standard type	10.16-mm pitch TLPXXXF type
Creepage Distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation Thickness	0.4 mm (min)	0.4 mm (min)

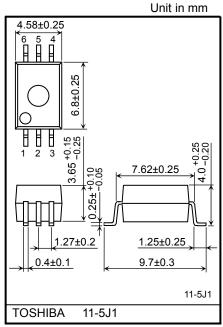
• UL recognized : UL1577, File No. E67349

Option (D4) type

TÜV approval : EN60747-5-2 under plan

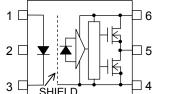
Truth Table

Input	LED	M1	M2	Output
Н	ON	ON	OFF	Н
L	OFF	OFF	ON	L



Weight: 0.26 g (typ.)

Pin Configuration (Top View)



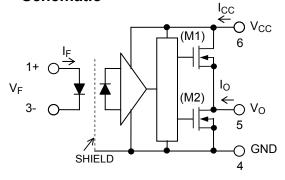
1: ANODE 2: N.C

3: CATHODE 4: GND

5: V_O (OUTPUT)

6: V_{CC}

Schematic



A 0.1- μ F bypass capacitor must be connected between pins 6 and 4. (See Note 6.)

Absolute Maximum Ratings (Ta = 25 °C)

	Characteristics	Symbol	Rating	Unit	
	Forward current	lF	20	mA	
	Forward current derating (Ta ≥ 85°	∆l _F /∆Ta	-0.54	mA/°C	
LED	Peak transient forward current	(Note 1)	IFP	1	Α
	Reverse voltage		V_{R}	6	V
	Junction temperature		Tj	125	°C
	"H" peak output current	I _{OPH}	-2.0	Α	
or	"L" peak output current	(Note 2)	I _{OPL}	2.0	Α
Detector	Output voltage	Vo	35	V	
De	Supply voltage		V _{CC}	35	V
	Junction temperature		Tj	125	°C
Oper	rating frequency	(Note 3)	f	50	kHz
Oper	ating temperature range	T _{opr}	-40~100	°C	
Stora	age temperature range	T _{stg}	-55~125	°C	
Lead	Lead soldering temperature (10 s) (Note 4)			260	°C
Isola	tion voltage (AC, 1 minute, R.H. ≤ 6	(Note 5)	BVS	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Pulse width $P_W \le 1 \mu s$, 300 pps
- Note 2: Exponential waveform pulse width $P_W \le 0.3 \mu s$, $f \le 15 \text{ kHz}$
- Note 3: Exponential waveform I_{OPH} ≤−1.5 A (≤ 0.3 μs), I_{OPL} ≤+1.5 A (≤ 0.3 μs), Ta=100°C
- Note 4: For the effective lead soldering area
- Note 5: Device considered a two-terminal device: pins 1, 2 and 3 paired with pins 4, 5 and 6 respectively.
- Note 6: A ceramic capacitor $(0.1 \, \mu F)$ should be connected from pin 6 to pin 4 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.

Recommended Operating Conditions

Characteristics		Symbol	Min	Тур.	Max	Unit
Input current, ON	(Note 7)	I _{F (ON)}	7.5	_	10	mA
Input voltage, OFF		V _{F (OFF)}	0		0.8	٧
Supply voltage *	(Note 8)	V _{CC}	15	_	30	V
Peak output current		I _{OPH} / I _{OPL}	_	_	± 1.5	Α
Operating temperature		T _{opr}	-40	_	100	°C

^{*} This item denotes operating ranges, not meaning of recommended operating conditions.

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note 7: Input signal rise time (fall time) $\leq 0.5 \mu s$.

Note 8: If the Vcc rise slope is sharp, an internal circuit might not operate with stability. Please design the Vcc rise slope under $3.0 \text{ V/}\mu\text{s}$.

Electrical Characteristics (Ta = $-40^{\circ}100$ °C, unless otherwise specified)

Characteristics	i	Symbol	Test Circuit	Test Condition		Min	Typ.*	Max	Unit
Forward voltage		V _F	_	I _F = 10 mA, Ta =	25 °C	_	1.57	1.75	V
Temperature coefficient of voltage	forward	ΔV _F /ΔTa	_	I _F = 10 mA		_	-2.0	_	mV/°C
Input reverse current		I _R		V _R = 6 V, Ta = 2	5 °C	_	_	10	μА
Input capacitance		C _T	_	V =0 V, f = 1 MH:	z, Ta = 25 °C	_	100	_	pF
	"H" Level	I _{OPH1}	1	V _{CC} = 15 V	V ₆₋₅ = -3.5 V	-1.0	-1.4	_	
Output current	n Levei	I _{OPH2}	I	$I_F = 5 \text{ mA}$	V ₆₋₅ = -7 V	-1.5		_	
(Note 9)	"!"!!	I _{OPL1}	2	V _{CC} = 15 V	V ₅₋₄ = 2.5 V	1.0	1.4	_	A .
	"L" Level	I _{OPL2}	2	$I_F = 0 \text{ mA}$	V ₅₋₄ = 7 V	1.5	_	_	
	"H" Level	V _{OH}	3	VCC1=+15V, VEE1=-15V R _L = 200Ω, I _F = 5 mA		11	13.7	_	V
Output voltage	"L" Level	V _{OL}	4	VCC1=+15V, VEE1=-15V $R_L = 200\Omega, V_F = 0.8 \text{ V}$		_	-14.9	-12.5	
Complete accompany	"H" Level	Icch	5	V _{CC} = 30 V	I _F = 10 mA	_	1.3	2.0	
Supply current	"L" Level	ICCL	6	V _O =Open	I _F = 0 mA	_	1.3	2.0	mA
Threshold input current	$L \rightarrow H$	I _{FLH}	_	V _{CC} = 15 V, V _O ?	> 1 V		1.8	5	mA
Threshold input voltage	$H \rightarrow L$	V _{FHL}		V _{CC} = 15 V, V _O < 1 V		0.8		_	V
Supply voltage		V _{CC}	_	_		15	_	30	V
		V _{UVLO+}	_	V _O > 2.5V	, IF = 5 mA	11.0	12.5	13.5	V
UVLO thresh hold		V _{UVLO-}	_	V _O < 2.5V, IF = 5 mA		9.5	11.0	12.0	V
UVLO hysteresis		UVLO _{HYS}	_	_		_	1.5	_	V

(*): All typical values are at Ta = 25°C

Note 9: Duration of lo time \leq 50 μ s, 1 pulse

Note 10: This product is more sensitive than conventional products to electrostatic discharge (ESD) owing to its low power consumption design.

It is therefore all the more necessary to observe general precautions regarding ESD when handling this component.

Isolation Characteristics (Ta = 25 °C)

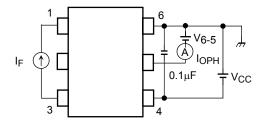
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	Vs = 0 V , f = 1MHz (Note 5)	_	1.0	_	pF
Isolation resistance	R _S	R.H. ≤ 60 %, V _S = 500 V (Note 5)	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage	BVS	AC, 1 minute	5000	_	_	Vrms
		AC, 1 second, in oil	_	10000	_	VIIIIS
		DC, 1 minute, in oil		10000	_	Vdc

Switching Characteristics (Ta = -40~100 °C, unless otherwise specified)

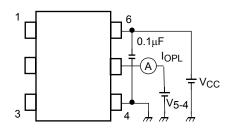
Characteristics		Symbol	Test Circuit	Test Co	Test Condition		Typ.*	Max	Unit
Propagation delay time	$L \rightarrow H$	^t pLH			$I_F = 0 \rightarrow 5 \text{ mA}$	50	_	500	
Tropagation delay time	$H \rightarrow L$	L t _{pHL} V _{CC} = 30 V	$I_F = 5 \rightarrow 0 \text{ mA}$	50		500			
Output rise time (10–90 %) t _r		t _r	7	$R_g = 20 \Omega$	$I_F = 0 \rightarrow 5 \text{ mA}$	_	50		ns
Output fall time (90–10 %)		tf			$I_F = 5 \rightarrow 0 \text{ mA}$	_	50	_	
Switching time dispersion between ON and OFF		tpHL-tpLH	IF		$I_F = 0 \leftrightarrow 5 \text{ mA}$			250	
Common mode transient i at HIGH level output	mmunity	CM _H	8	V _{CM} =1000 Vp-p	$I_F = 5 \text{ mA}$ $V_{O \text{ (min)}} = 26 \text{ V}$	-10000			V/µs
Common mode transient immunity at LOW level output		CML	0		I _F = 0 mA V _{O (max)} = 1 V	10000			ν/μ5

^{(*):} All typical values are at Ta = 25 °C.

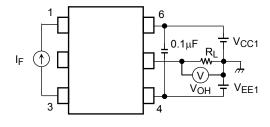
Test Circuit 1: IOPH



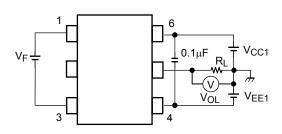
Test Circuit 2: IOPL



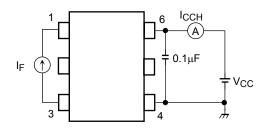
Test Circuit 3: V_{OH}



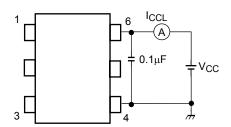
Test Circuit 4: V_{OL}



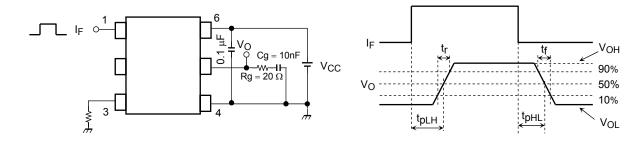
Test Circuit 5: Icch



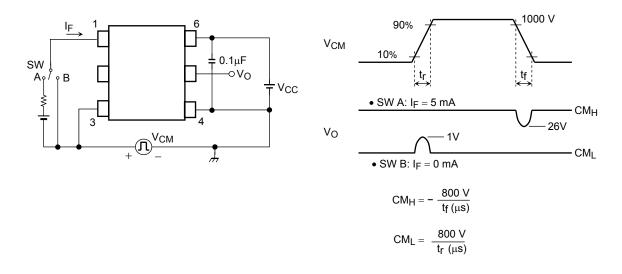
Test Circuit 6: I_{CCL}



Test Circuit 7: t_{pLH} , t_{pHL} , t_r , t_f , $\mid t_{pHL}$ - $t_{pLH} \mid$



Test Circuit 8: CMH, CML



 CM_L (CM_H) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the LOW (HIGH) state.

RESTRICTIONS ON PRODUCT USE

20070701-EN

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